NSN 5961-01-533-9986

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-533-9986 **Inclosure Material:** Metal **Overall Length:** Between 0.225 inches and 0.255 inches **Terminal Length:** 0.500 inches **Overall Diameter:** Between 0.209 inches and 0.230 inches **Function For Which Designed:** Phototransistor **End Application:** An/frt-31, transmitting set, radio **Mounting Method: Terminal Terminal Circle Diameter:** 0.510 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 45.0 breakdown voltage, collector to emitter, sustained and 45.0 collector to base voltage/static/emitter open and 5.0 emitter to base voltage, static, collector open **Current Rating Per Characteristic:** 0.50 milliamperes service voltage **Power Rating Per Characteristic:** 600.0 milliwatts small-signal input power, common-emitter peak **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Product Name:** Hermetic silicon phototransistor **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:**

No ---

Fiig:

A110a0